

40V PNP LOW POWER TRANSISTOR IN SOT23

Features

- BV_{CEO} > -40V
- BV_{ECO} > --3V
- I_C = -1.5A Continuous Collector Current
- V_{CE(sat)} < -115mV @ -1A
- R_{CE(sat)} = 82mΩ
- High Peak Current
- Complementary Part Number ZXTN25040DFL
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 <a>®
- Weight: 0.008 grams (Approximate)

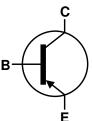
Applications

- MOSFET and IGBT Gate Driving
- DC-DC Converters

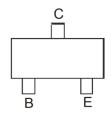
SOT23



Top View



Device Symbol



Top View Pin-Out

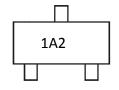
Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTP25040DFLTA	1A2	7	8	3,000

Notes:

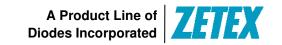
- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



1A2 = Product Type Marking Code





Absolute Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-45	V
Collector-Emitter Voltage (Forward Blocking)	V _{CEO}	-40	V
Emitter-collector voltage (Reverse Blocking)	V _{ECO}	-3	V
Emitter-Base Voltage	V_{EBO}	-7	V
Continuous Collector Current (Note 5)	lc	-1.5	Α
Base Current	I _B	-500	mA
Peak Pulse Current	Ісм	-5	Α

Thermal Characteristics (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)	D-	310	mW	
Power Dissipation	(Note 6)	P _D	350		
Thermal Resistance, Junction to Ambient	(Note 5)	D	403		
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	357	C/VV	
Thermal Resistance, Junction to Leads (Note 7)		$R_{ heta JL}$	350	°C/W	
Operating and Storage Temperature Range		$T_{J_i}T_{STG}$	-55 to +150	℃	

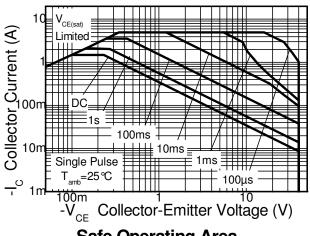
ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

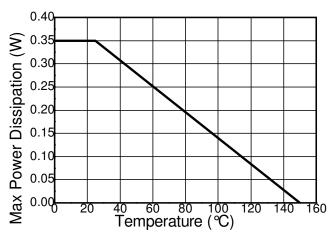
- 5. For a device mounted on minimum recommended pad layout 1oz copper that is on a single-sided FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Same as Note 5, except the device is mounted on 15 mm x 15mm 1oz copper.
 7. Thermal resistance from junction to solder-point (at the end of the leads).
 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



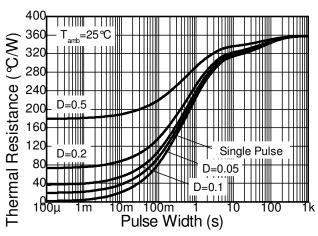
Thermal Characteristics and Derating Information



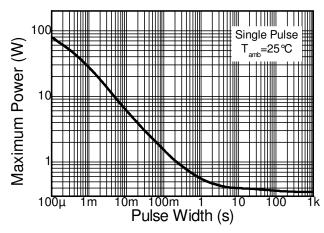
Safe Operating Area



Derating Curve



Transient Thermal Impedance



Pulse Power Dissipation



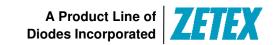


Electrical Characteristics (@T_A = +25 °C, unless otherwise specified.)

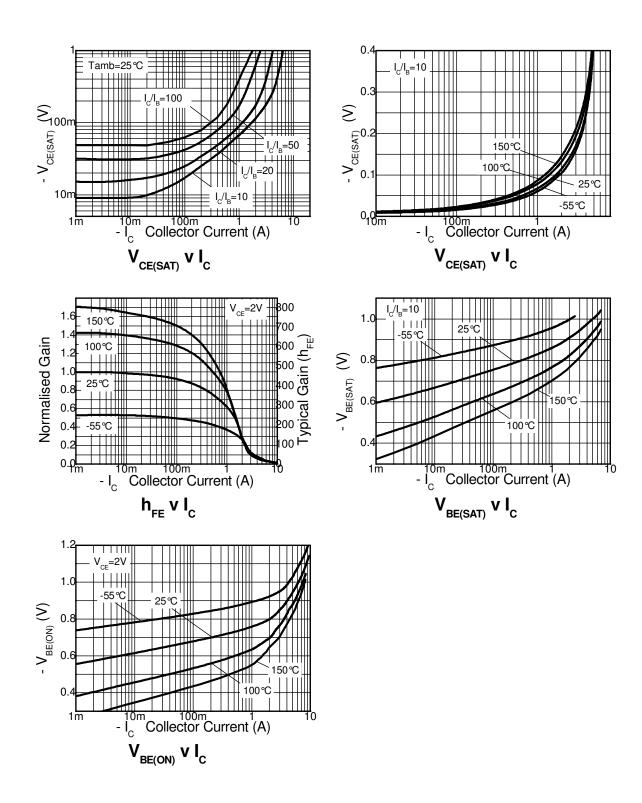
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_CBO	-45	-75	-	V	$I_{C} = -100 \mu A$
Collector-Emitter Breakdown Voltage (Note 9)	BV_CEO	-40	-65	-	V	I _C = -10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	-8.2	-	V	$I_E = -100\mu A$
Emitter-Base Breakdown Voltage	BV _{ECO}	-3	-8.7	-	V	$I_E = -100\mu A$
Collector-Base Cutoff Current	I _{CBO}	-	< -1	-50	nA	V _{CB} = -36V
Collector-base Cuton Current		-	-	-20	μΑ	V _{CB} = -36V, T _{amb} = +100 ℃
Emitter-Base Cutoff Current	I _{EBO}	-	< -1	-50	nA	$V_{EB} = -5.6V$
		300	450	900		$I_C = -10$ mA, $V_{CE} = -2$ V
Static Forward Current Transfer Ratio (Note 9)	hee	120	200	-	_	$I_C = -1.5A, V_{CE} = -2V$
Static Forward Guitent Transfer Fratio (Note 9)	h _{FE}	15	40	-	-	$I_C = -3A$, $V_{CE} = -2V$
			7.5	0.5		
	V _{CE(sat)}	-	-75	-95	mV	$I_C = -0.5A$, $I_B = -20mA$
		-	-200	-290		$I_C = -1A, I_B = -20mA$
Collector-Emitter Saturation Voltage (Note 9)		-	-95	-115		$I_C = -1A$, $I_B = -100mA$
		-	-160	-190		$I_C = -1.5A$, $I_B = -75mA$
		-	-245	-300		$I_C = -3A$, $I_B = -300mA$
Base-Emitter Saturation Voltage (Note 9)	$V_{BE(sat)}$	-	-915	-1000	mV	$I_C = -1.5A$, $I_B = -75mA$
Base-Emitter Saturation Voltage (Note 9)	$V_{BE(on)}$	-	-825	-900	mV	$I_C = -1.5A, V_{CE} = -2V$
Output Capacitance	C_obo	-	17.4	25	рF	$V_{CB} = -10V$, $f = 1MHz$
Transition Frequency	f _T	-	270	-	MHz	$V_{CE} = -10V, I_{C} = -50mA,$ f = 50MHz
Delay Time	t _(d)	-	34	-	ns	
Rise Time	t _(r)	-	41	-	ns	$V_{CC} = -15V, I_{C} = -750mA,$
Storage Time	t _(s)	-	266	-	ns	$I_{B1} = -I_{B2} = -15mA$
Fall Time	$t_{(f)}$	-	53	-	ns	

Notes: 9. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.





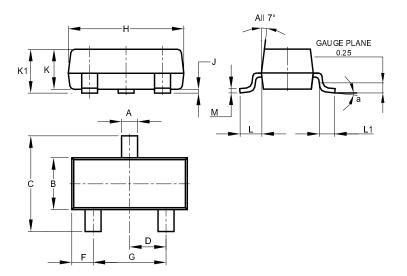
Typical Electrical Characteristics (@T_A = +25 ℃, unless otherwise specified.)





Package Outline Dimensions

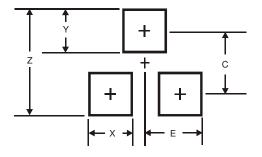
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT23					
Dim	Min	Max	Тур		
Α	0.37	0.51	0.40		
В	1.20	1.40	1.30		
С	2.30	2.50	2.40		
D	0.89	1.03	0.915		
F	0.45	0.60	0.535		
G	1.78	2.05	1.83		
Н	2.80	3.00	2.90		
J	0.013	0.10	0.05		
K	0.890	1.00	0.975		
K1	0.903	1.10	1.025		
L	0.45	0.61	0.55		
L1	0.25	0.55	0.40		
М	0.085	0.150	0.110		
а	8°				
All	All Dimensions in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
Z	2.9		
X	0.8		
Υ	0.9		
С	2.0		
E	1.35		





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